

We claim:

SUB A, > 1. A method for removing structures, which comprises the steps of:

providing a substrate having the structures to be removed;

depositing a sacrifice layer on the structures and the substrate; and

removing the structures and the sacrifice layer in a polishing step.

2. The method according to claim 1, which comprises forming the structures from a material selected from the group consisting of noble metals, oxides of noble metals, dielectric materials and ferroelectric materials.

SUB B, > 3. The method according to claim 1, which comprises forming the structures that must be removed with an aspect ratio of greater than 2.

4. The method according to claim 1, which comprises carrying out a chemical mechanical polishing process as the polishing step.

5. The method according to claim 1, which comprises forming the sacrifice layer from at least one of a silicon oxide layer and a silicon nitride layer.

6. The method according to claim 4, which comprises removing residues of the sacrifice layer by wet chemical processes following the chemical mechanical polishing process.

7. The method according to claim 1, which comprises forming the structures that must be removed with an aspect ratio of greater than 4.

8. A method for producing at least one structured layer, which comprises the steps of:

providing a substrate;

applying at least one layer to the substrate for structuring;

applying a mask to the layer to be structured;

etching the layer being structured by a dry etching method, so that redepositions of the layer emerge at sidewalls of the mask;

removing the mask;

applying a sacrifice layer; and

performing a polishing step to remove the redepositions of the layer being structured, and to remove the sacrifice layer, so that a structured layer emerges.

50/101/ 9. The method according to claim 8, which comprises forming the layer from a material selected from the group consisting of noble metals, an oxide of the noble metals, a dielectric material and a ferroelectric material.

10. The method according to claim 8, which comprises interrupting the polishing step and removing residues of the mask.

11. The method according to claim 8, which comprises performing a chemical mechanical polishing process as the polishing step.

12. The method according to claim 8, which comprises forming the sacrifice layer from at least one of a silicon oxide layer and a silicon nitride layer.